

### ABSTRACT OF THE DISCLOSURE

Provided is a capacitor of a semiconductor device. The capacitor includes a capacitor lower electrode disposed on a semiconductor substrate. A first dielectric layer comprising aluminum oxide ( $\text{Al}_2\text{O}_3$ ) is disposed on the capacitor lower electrode. A second dielectric layer comprising a material having a higher dielectric constant than that of aluminum oxide is disposed on the first dielectric layer. A third dielectric layer comprising aluminum oxide is disposed on the second dielectric layer. A capacitor upper electrode is disposed on the third dielectric layer. The capacitor of the present invention can improve electrical properties.

Thus, power consumption can be reduced and capacitance per unit area is high enough to achieve high integration.